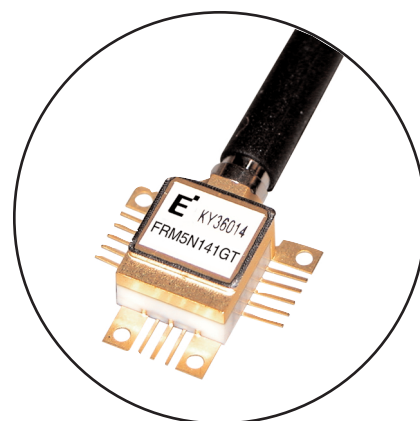


FEATURES

- Board mount type “GT” package: 17 pins
- InGaAs-APD with pre-amplifier
- Integrated Design Optimizes Performance at Bit Rates up to 10.7Gb/s
- Electrical Differential Output
- High Sensitivity: -26.5dBm
- Operates in both C and L wavelength bands



APPLICATIONS

This APD with preamplifier is intended to function as an optical receiver at 1,310nm or 1,530-1,610nm in SONET, SDH, DWDM or other optical fiber systems operating up to 10.7Gb/s. The typical transimpedance (Z_t) value of 1,200 Ω optimizes the total bandwidth for 10Gb/s application. The detector preamplifier is DC coupled and has an electrical differential output.

DESCRIPTION

The FRM5N141GT incorporates a high bandwidth InGaAs APD photo diode, a GaAs amplifier in a hermetically sealed board mount type package. The APD is processed with modern epitaxial techniques resulting in a reliable performance over a wide range of operating conditions.

ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Ratings		Unit
		Min.	Max.	
Storage Temperature	T_{stg}	-40	+85	$^\circ\text{C}$
Operating Temperature	T_{op}	-5	+75	$^\circ\text{C}$
Supply Voltage	V_{ss}	-6	0	V
APD Reverse Voltage	V_R	0	$V_B(\text{Note})$	V
APD Reverse Current	I_R	-	4(peak)	mA

Note: Since V_B may vary from device-to-device, V_B data is attached to each device for reference.

OPTICAL & ELECTRICAL CHARACTERISTICS

(T_C=25°C, λ=1,550nm, V_{SS}=-5.2V, unless otherwise specified)

Parameter	Symbol	Test Conditions		Limits			Unit
				Min.	Typ.	Max.	
APD Responsivity	R	λ = 1,310nm, M=1		0.75	0.85	-	A/W
		λ = 1,550nm, M=1		0.75	0.90	-	
		λ = 1,610nm, M=1		-	0.80	-	
APD Breakdown Voltage	VB	ID = 10μA		20.0	25.0	30.0	V
Temperature Coefficient of VB	Γ	Note (1)		0.03	0.05	0.07	V/°C
AC Transimpedance	Z _t	f = 750MHz, Single-end		800	1200	-	Ω
Maximum Output Voltage Swing	V _{clip}	Saturated Output Voltage		350	550	750	mV
Bandwidth	BW	-3dB from 750MHz, Pin=-20dBm	M=9	6.0	7.5	8.5	GHz
			M=3	6.0	7.5	-	
Lower Cut-off Frequency	f _{cl}	-3dB from 750MHz, Pin=-20dBm		-	40	100	kHz
Peaking	d _{pk}	130MHz to BW, Pin=-20dBm, M=9		-	0.5	-	dB
Group Delay Deviation	GD	1GHz to 4GHz, Pin=-20dBm, M=9		-	30	-	ps _{p-p}
		1GHz to 6GHz, Pin=-20dBm, M=9		-	50	-	
Output Return Loss	S ₂₂	130MHz to 6GHz		-	12	-	dB
		130MHz to 8GHz		-	7	-	
Minimum Sensitivity	P _r	10Gb/s, NRZ, PRBS=2 ³¹ -1, B.E.R.=10 ⁻¹² , VR=Optimum, Rext=13dB	25°C	-	-26.5	-25.0	dBm
			75°C	-	-25.5	-24.0	
Maximum Overload	P _O	10Gb/s, NRZ, PRBS=2 ³¹ -1, B.E.R.=10 ⁻¹² , M=3, Rext=13dB		-7	-5	-	dBm
Optical Return Loss	ORL	λ = 1,550nm		27	-	-	dB
		λ = 1,310nm		27	-	-	
Power Supply Current	I _{SS}	-		-	110	130	mA
Power Supply Voltage	V _{SS}	-		-5.46	-5.20	-4.94	V
Thermistor Resistance	R _{th}	-		9.5	10.0	10.5	kΩ
Thermistor B Constant	B	-		3800	3900	4000	K

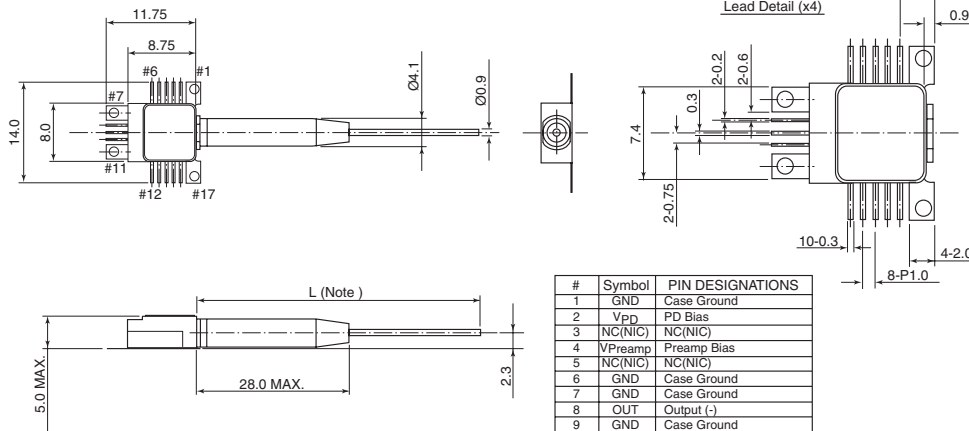
Note 1: Γ=ΔVB/dTc

Note: All the parameters are measured with 50Ω load through external coupling capacitor.

Notes

"GT" PACKAGE

UNIT: mm



#	Symbol	PIN DESIGNATIONS
1	GND	Case Ground
2	V _{pp}	PD Bias
3	NC(NIC)	NC(NIC)
4	VPreamp	Preamp Bias
5	NC(NIC)	NC(NIC)
6	GND	Case Ground
7	GND	Case Ground
8	OUT	Output (-)
9	GND	Case Ground
10	OUT	Output (+)
11	GND	Case Ground
12	GND	Case Ground
13	OFFSET	DC Offset Control
14	NC(NIC)	NC(NIC)
15	NC(NIC)	NC(NIC)
16	R _{th}	Thermistor for APD
17	GND	Case Ground

NC (NIC): No Internal Connection

Note: The fiber length (L) shall be specified in the detail (individual) specification.

For further information please contact:

Eudyna Devices USA Inc.

2355 Zanker Rd.
San Jose, CA 95131-1138, U.S.A.
TEL: (408) 232-9500
FAX: (408) 428-9111
www.us.eudyna.com

Eudyna Devices Europe Ltd.

Network House
Norreys Drive
Maidenhead, Berkshire SL6 4FJ
United Kingdom
TEL: +44 (0) 1628 504800
FAX: +44 (0) 1628 504888

Eudyna Devices Asia Pte Ltd.

Hong Kong Branch
Rm. 1101, Ocean Centre, 5 Canton Rd.
Tsim Sha Tsui, Kowloon, Hong Kong
TEL: +852-2377-0227
FAX: +852-2377-3921

Eudyna Devices Inc.

Sales Division
1, Kanai-cho, Sakae-ku
Yokohama, 244-0845, Japan
TEL: +81-45-853-8156
FAX: +81-45-853-8170

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